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Belyaev, A.E., Ya.F. Kononetz, Yu.G. Semenov and N.A. Vlasenko, Magnetic effects in electroluminescence of ZnS : Mn films 101 (1990) 985
Benachemhou, A., see Achargui 107 (1991) 410
Benakki, S., see Wu 102 (1990) 701
Benalloul, P., J. Benoit, A. Geoffroy, D. Yebdri, R. Bilewicz, W. Busse, H.-E. Gumlich and R. Rebentisch, Thin film electroluminescence of $Zn_{1-x}Mn_xS_{1-y}Te_y$ 101 (1990) 976
Benalloul, P., J. Benoit, R. Mach, G.O. Müller and G.U. Reinsperger, Decay of ZnS : Mn emission in thin films – revisited 101 (1990) 989
Benchimol, J.L., F. Alaoui, Y. Gao, G. Le Roux, E.V.K. Rao and F. Alexandre, Chemical beam epitaxy of indium phosphide 105 (1990) 135
Benchimol, J.L., G. Le Roux, H. Thibierge, C. Daguet, F. Alexandre and F. Brillouet, Incorporation of group III and group V elements in chemical beam epitaxy of GaInAsP alloys 107 (1991) 978
Bender, H., see Lin 104 (1990) 653
Benecke, C., see Heimbrodt 101 (1990) 911
Benecke, C., W. Busse and H.-E. Gumlich, Chemical trends of the luminescence in wide band gap $II_{1-x}Mn_xVI$ semimagnetic semiconductors 101 (1990) 931
Beneking, H., see Gruhle 110 (1991) 985
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Bennema, P. and O. Söhnel, Interfacial surface tension for crystallization and precipitation from aqueous solutions 102 (1990) 547
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Bensaoula, A., H. Hansen, H.C. Chen, J.T. Zborowski, K.D. Jamison, A. Ignatiev, H.D. Shih and Y.K. Tao, A RHEED and XPS study of $In_xGa_{1-x}As$ on GaAs grown by chemical beam epitaxy 105 (1990) 227

Benton, J.L., Characterization of defects in semiconductors by deep level transient spectroscopy 106 (1990) 116

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Bergmann, R., Model for defect-free epitaxial lateral overgrowth of Si over SiO_2 by liquid phase epitaxy 110 (1991) 823

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Berkovitch-Yellin, Z., H.A.S. Hansen, W.S. Bennett, R. Sharon, K. von Boehlen, N. Volkmann, J. Piefke, A. Yonath and H.G. Wittmann, Crystals of 70S ribosomes from thermophilic bacteria are suitable for X-ray analysis at low resolution 110 (1991) 208

Berkowski, M., see Iliev 108 (1991) 219

Berkowski, M., K. Iliev, V. Nikolov, P. Peshev and W. Piekarczyk, Conditions of maintenance of a flat crystal/melt interface during Czochralski growth of bismuth germanium oxide single crystals 108 (1991) 225

Berkstresser, G.W., A.J. Valentino and C.D. Brandle, Growth of single crystals of rare earth gallates 109 (1991) 457

Berkstresser, G.W., A.J. Valentino and C.D. Brandle, Growth of single crystals of lanthanum aluminate 109 (1991) 467

Berlouis, L.E.A., L.M. Peter, D.J. Diskett, A.J. Avery, M.G. Astles, J. Giess and N.T. Gordon, Characterisation of epitaxial $Cd_xHg_{1-x}Te$ using electrolyte electroreflectance with in-situ electrochemical etching 101 (1990) 153

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Bernussi, A.A., F. Iikawa, P. Motisuke and P. Basmaji, Properties of $Al_xGa_{1-x}As$ with an AlAs buffer layer on Si substrates grown by metalorganic vapor phase epitaxy 108 (1991) 615

Bertho, D., A. Simon, D. Boiron, C. Jouanin and C. Priester, Calculation of band offsetts in strained II–VI heterojunctions 101 (1990) 372

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Bevan, M.J., N.J. Doyle and D. Snyder, A comparison of $Hg_{1-x}Cd_xTe$ MOCVD films on lattice-matched (CdZn)Te and Cd(TeSe) substrates 102 (1990) 785

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Bhat, R., E. Kapon, S. Simhony, E. Colas, D.M. Hwang, N.G. Stoffel and M.A. Koza, Quantum wire lasers by OMCVD growth on nonplanar substrates 107 (1991) 716

Bhat, R., C. Caneau, C.E. Zah, M.A. Koza, W.A. Bonner, D.M. Hwang, S.A. Schwarz, S.G. Menocal and F.G. Favire, Orientation dependence of S, Zn, Si, Te, and Sn doping in OMCVD growth of InP and GaAs: application to DH lasers and lateral p–n junction arrays grown on non-planar substrates 107 (1991) 772

Bhat, R., M.A. Koza, C.E. Zah, C. Caneau, C.C. Chang, S.A. Schwarz, A.S. Gozdz, P.S.D. Lin and A. Yi-Yan, A novel technique for the preservation of gratings in InP and InGaAsP and for the simultaneous preservation of InP, InGaAs, and InGaAsP in OMCVD 107 (1991) 871

Bhat, R., M.A. Koza, K. Kash, S.J. Allen, W.P. Hong, S.A. Schwarz, G.K. Chang and P. Lin, Growth of high quality AlInAs by low pressure organometallic chemical vapor deposition for high speed and optoelectronic device applications 108 (1991) 441

Bhat, R., M.A. Koza, D.M. Hwang, K. Kash, C. Caneau and R.E. Nahory, The growth of GaInAs/InP and GaInAs/AlInAs superlattices with thin barrier layers by low pressure organometallic chemical vapor deposition 110 (1991) 353

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Biefeld, R.M., J.R. Wendt and S.R. Kurtz, Improving the performance of $InAs_{1-x}Sb_x$/InSb infrared detectors grown by metalorganic chemical vapor deposition 107 (1991) 836

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Bischopink, G. and K.W. Benz, Growth of $Al_xGa_{1-x}Sb$ bulk material from metallic solution 108 (1991) 465
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Bishop, J.B., J.C. Martin and W.M. Rosenblum, A light scattering method for qualitatively monitoring aggregation rates in macromolecular systems 110 (1991) 164
Bishop, S.G. and J.A. Freitas, Jr., Photoluminescence characterization of cubic SiC grown by chemical vapor deposition on Si substrates 106 (1990) 38
Bivas, A., W.L. Smith, R.R. Kola, Z.J. Radzimski and G.A. Rozgonyi, Thermal wave imaging of misfit dislocations and correlation with minority carrier lifetime 103 (1990) 200
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Bohling, D.A., G.T. Muhr, C.R. Abernathy, A.S. Jordan, S.J. Pearton and W.S. Hobson, The search for all-hydride MOMBE: examination of trimethylamine alane, trimethylamine gallane, and arsine 107 (1991) 1068
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Bolt, R.J., H. de Haas, M.T. Sebastian and H. Klapper, Characterization of flux-grown $KTiOPO_4$ (KTP) crystals by X-ray topography 110 (1991) 587
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Borodin, V.A., V.V. Sidorov, S.N. Rossolenko, T.A. Steriopolo, V.A. Tatarchenko and T.N. Yalovets, Local shaping technique and new growth apparatus for complex sapphire products 104 (1990) 69
Borodin, V.A., M.Yu. Starostin and T.N. Yalovets, Structure and related mechanical properties of shaped eutectic Al_2O_3–$ZrO_2(Y_2O_3)$ composites 104 (1990) 148
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Growth of large, high-quality beta-barium metaborate crystals 108 (1991) 394

Bottka, N., D.K. Gaskill, P.D. Wright, R.W. Kaliski and D.A. Williams, Qualification of OMVPE AlGaAs/GaAs HBT structures using nondestructive photoreflectance spectroscopy 107 (1991) 893

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Bougnot, G., F. Delannoy, F. Pascal, P. Grosse, A. Giani, J. Kaoukab, J. Bougnot, R. Fourcade, P.J. Walker, N.J. Mason and H. Lambert, Improvement of the crystalline, optical and electrical quality of MOVPE GaInSb layers 107 (1991) 502

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Boulanger, D. and R. Parrot, Ligand-field theory for the orbit–lattice and spin–lattice coupling coefficients of Mn^{2+} in ZnS and ZnSe 101 (1990) 368

Boulliard, J.C. and M.P. Sotto, On the relations between surface structures and morphology of crystals 110 (1991) 878

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Bourret, E.D., J.B. Guitron, M.L. Galiano and E.E. Haller,. Vertical seeded melt growth of GaAs 102 (1990) 877

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Brandt, G., H. Ennen, R. Moritz and W. Rothemund, Characterization of CdTe crystals by chemical etching and cathodoluminescence measurements 101 (1990) 226

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Brantov, S.K., K.N. Filonov, B.M. Epelbaum, L.V. Miheeva and A.M. Sitnikov, Development of the two-shaping-elements (TSE) method for silicon sheet growth 104 (1990) 98

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Bruines, J.J.P., J. Le Bris, M. Renaud and M. Erman, Spatially-resolved photoluminescence study of InP:Fe substrates from different suppliers 102 (1990) 769
Bruno, A. and J.P. Lascaray, Nearest and next nearest neighbor exchange interaction between magnetic ions in II–VI semimagnetic semiconductors 101 (1990) 936
Brush, L.N., S.R. Coriell and G.B. McFadden, Directional solidification of a planar interface in the presence of a time-dependent electric current 102 (1990) 725
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Buchan, N.I. and J.M. Jasinski, Calculation of unimolecular rate constants for common metalorganic vapor phase epitaxy precursors via RRKM theory 106 (1990) 227
Buchan, N.I., T.F. Kuech, M.A. Tischler and R. Potemski, Epitaxial growth of GaAs with $(C_2H_5)_2GaCl$ and AsH_3 in a hot-wall system 107 (1991) 331
Buchan, N.I., T.F. Kuech, G. Scilla and F. Cardone, Carbon incorporation in metal-organic vapor phase epitaxy grown GaAs using CH_yX_{4-y}, TMG and AsH_3 110 (1991) 405
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Burger, A., D.O. Henderson, S.H. Morgan and E. Silberman, Purification, crystal growth and characterization of CdSe single crystals 109 (1991) 304
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Burns, R.C., V. Cvetkovic, C.N. Dodge, D.J.F. Evans, M.L.T. Rooney, P.M. Spear and C.M. Welbourn, Growth-sector dependence of optical features in large synthetic diamonds 104 (1990) 257
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Busse, W., see Benalloul 101 (1990) 976
Butler, B.R., A.T.R. Briggs, S.A. Kitching and A. Chew, Hydrogen passivation during cooling of p-type InP grown by metal-organic vapour phase epitaxy, due to a combined reaction between phosphine and dimethylzinc 102 (1990) 393
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Button, C.C., see Roberts 107 (1991) 915
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Buyevich, Yu.A. and V.V. Mansurov, Kinetics of the intermediate stage of phase transition in batch crystallization 104 (1990) 861
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Cacioppo, E., S. Munson and M.L. Pusey, Protein solubilities determined by a rapid technique and modification of that technique to a micro-method 110 (1991) 66
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Calzadilla, O., O. de Melo, J. Fuentes, S. Lopez, R. Zabala, F. Leccabue, B.E. Watts and P. Franzosi, Growth, morphological and structural characterization of $Pb_{1-x}Sn_xTe$ single crystals 110 (1991) 968
Camarda, R.M., see Yang 105 (1990) 162
Camassel, J., see Achargui 107 (1991) 410
Camassel, J., J.P. Laurenti, S. Juillaguet, F. Reinhardt, K. Wolter, H. Kurz and D. Grützmacher, Finite interface effects for thin GaInAs/InP quantum wells grown by LP-MOVPE with a growth interruption sequence 107 (1991) 543
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Caneau, C., H.J. Yoo, R. Bhat, M. Koza and

J.R. Hayes, Selective in situ etching of GaInAsP for improved growth interfaces 102 (1990) 491
Caneau, C., R. Bhat, M. Koza, J.R. Hayes and R. Esagui, Etching of InP by HCl in an OMVPE reactor 107 (1991) 203
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Cao, D.S., E.H. Reihlen, G.S. Chen, A.W. Kimball and G.B. Stringfellow, Effect of growth rate on properties of $Ga_{0.51}In_{0.49}P$ grown by organometallic vapor phase epitaxy 109 (1991) 279
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Capper, P., W.G. Coates, C.L. Jones, J.J.G. Gosney, I. Kenworthy and C.K. Ard, Effect of process changes on the properties of $Cd_xHg_{1-x}Te$ crystals grown by Bridgman using ACRT 102 (1990) 848
Caram, R., S. Chandrasekhar and W.R. Wilcox, Influence of convection on rod spacing of eutectics 106 (1990) 294
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Carlson, D.J. and A.F. Witt, Microsegregation in conventional Si-doped LEC GaAs 108 (1991) 508
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Cerreta, M.K. and K.A. Berglund, Contact nuclei formation in aqueous dextrose solutions 102 (1990) 869
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Chan, H.-K., I. Gonda and A.J. McLachlan, Studies of the mechanism of crystal growth of hexamethylmelamine. I. Solute–solvent interactions 104 (1990) 355
Chan, H.-K. and I. Gonda, Studies of the mechanism of crystal growth of hexamethylmelamine. II. Rates of growth of the crystal faces 108 (1991) 751
Chand, N. and S.N.G. Chu, A comprehensive study and methods of elimination of oval defects in MBE-GaAs 104 (1990) 485
Chandra Shekar, N.V., K. Govinda Rajan, R.N. Vishwanath and S. Ramasamy, Single crystal growth of $Cu_xMo_6Se_8$ 104 (1990) 445
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Chang, T.Y., J.L. Zyskind, A.H. Dayem, J.F. Ferguson, J.W. Sulhoff and E.H. Westerwick, Properties of $(Zn_{1-x}Mn_x)_3As_{2-\delta x}$ epitaxially grown on InP 104 (1990) 463
Changkang Chen, B.M. Wanklyn and P. Ramasamy, The flux growth of scandium oxide crystals 104 (1990) 672
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Chattopadhyay, K. and N.K. Mukhopadhyay, On the origin of banded microstructure in rapidly solidified alloys: the case of Al–10%Mn quasicrystalline system 106 (1990) 387
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Chen, T.P., Y.D. Guo, T.S. Huang and L.J. Chen, Characteristics of facets in Si-doped GaAs crystals grown by horizontal Bridgman technique 103 (1990) 243
Chen, T.P., T.S. Huang, L.J. Chen and Y.D. Guo, The growth and characterization of GaAs single crystal by a modified horizontal Bridgman system 106 (1990) 367
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Chernov, A.A., N.P. Zaitseva and L.N. Rashkovich, Secondary nucleation induced by the cracking of a growing crystal: KH_2PO_4 (KDP) and $K(H,D)_2PO_4$ (DKDP) 102 (1990) 793
Cheuvart, P., U. El-Hanani, D. Schneider and R. Triboulet, CdTe and CdZnTe crystal growth by horizontal Bridgman technique 101 (1990) 270
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Chikaura, Y., M. Imai, Y. Suzuki and Y. Yatsurugi, Synchrotron X-radiation plane-wave topography for imaging microdefects in thinned silicon crystals 103 (1990) 141
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Chiu, T.H., J.E. Cunningham, J.A. Ditzenberger and W.Y. Jan, Growth and diffusion study of carbon doped GaAs superlattice grown by chemical beam epitaxy 107 (1991) 1051
Choe, K.S., see Stefani 106 (1990) 611
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Chu, C.H., L.J. Chen and H.L. Hwang, Formation of surface inversion layer in F^+-implanted n-type silicon 103 (1990) 188
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Chu, S.N.G., see Chand 104 (1990) 485
Chung, B.-C., R.T. Green and H.F. MacMillan, High carbon doping of $Al_xGa_{1-x}As$ ($0 \le x \le 1$) by atomic layer epitaxy 107 (1991) 89
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Ciszek, T.F., see Wang 109 (1991) 155
Ciszek, T.F. and C.D. Evans, Single-crystal growth and low-field AC magnetic susceptometry of $YBa_2Cu_3O_{7-\delta}$, $ErBa_2Cu_3O_{7-\delta}$, and $Bi_2Sr_2Ca_{0.8}Cu_2O_8$ superconductors 109 (1991) 418

Clancy, L.L., T.J. Rydel, S.W. Muchmore, D.R. Holland, K.D. Watenpaugh, B.C. Finzel and H.M. Einspahr, Crystal forms of a lysine-49 phospholipase A_2 from the eastern cottonmouth snake 104 (1990) 868
Clancy, L.L., see DeLucas 110 (1991) 302
Clapham, L., R.J.C. McLean, J.C. Nickel, J. Downey and J.W. Costerton, The influence of bacteria on struvite crystal habit and its importance in urinary stone formation 104 (1990) 475
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Colak, S., H. van Houten, T. Marshall and D.A. Cammack, Photo-Hall model for space charge effects in n-ZnSe/GaAs:Cr heterostructures 101 (1990) 828
Colas, E., D.E. Aspnes, R. Bhat, S.S. Studna, J.P. Harbison, L.T. Florez, M.A. Koza and V.G. Keramidas, In situ monitoring of crystal growth by reflectance difference spectroscopy 107 (1991) 47
Colas, E., A. Shahar, B.D. Soole, W.J. Tomlinson, J.R. Hayes, C. Caneau and R. Bhat, Lateral and longitudinal patterning of semiconductor structures by crystal growth on nonplanar and dielectric-masked GaAs substrates: application to thickness-modulated waveguide structures 107 (1991) 226
Colas, E., E.M. Clausen, Jr., E. Kapon, D.M. Hwang, S. Simhony, R. Bhat, C.Y. Chen, P.S.D. Lin, L. Schiavone and B. Van der Gaag, Direct evidence of lateral bandgap patterning on stepped structures grown on non-planar, vicinal GaAs surfaces by cathodoluminescence investigations 107 (1991) 243
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Cole, S., L. Davis, W.J. Duncan, E.M. Marsh, R.H. Moss, W.J.M. Rothwell, P.S. Skevington and G.D.T. Spiller, Doping level anomalies resulting from exposure to dopant precursors during cooling in MOVPE 107 (1991) 254
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Cureton, C.G., E.J. Thrush and A.T.R. Briggs, Lateral and vertical composition control in MOCVD-grown InP/GaInAs(P) structures 107 (1991) 549
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De Melo, O., O. Ori and C. Pelosi, The application of the Bragg–Williams model to the description of fundamental thermodynamical properties of binary semiconducting compounds 102 (1990) 141
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De Melo, O., F. Leccabue, R. Panizzieri, C. Pelosi, C. Bocelli, G. Calestani, V. Sagredo, M. Chourio and E. Paparazzo, CVT growth, thermodynamic and magneto-structural study of $Cd_{1-x}Mn_xTe$ single crystals 104 (1990) 780
De Melo, O., F. Leccabue, C. Pelosi, V. Sagredo, M. Chourio, J. Martin, G. Bocelli and G. Calestani, Crystal growth and characterization of MnTe single crystals 110 (1991) 445
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DeMattei, R.C. and R.S. Feigelson, The solubility dependence of canavalin on pH and temperature 110 (1991) 34
Demeester, P., L. Buydens, I. Moerman, D. Lootens and P. Van Daele, Non-planar MOVPE growth using a novel shadow-masking technique 107 (1991) 161
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Desai, C.C. and M.S.V. Ramana, Nucleation density and electrolytic growth of lead hydrogen phosphate single crystals in silica gels 102 (1990) 191
DeSisto, W.J. and R.L. Henry, Preparation and characterization of MgO thin films deposited by spray pyrolysis of Mg(2,4-pentanedionate)$_2$ 109 (1991) 314
Desjonquères, F., see Druilhe 101 (1990) 73
Desjonquères, F., A. Tromson-Carli, P. Cheuvart, R. Druilhe, C. Grattepain, A. Katty, Y. Marfaing, R. Triboulet and D. Lorans, Low temperature growth of (Cd,Hg)Te layers by MOVPE 107 (1991) 626
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Dietl, T., Transport properties of II–VI semimagnetic semiconductors 101 (1990) 808
Dilawari, A.H., J. Szekely and J. Daly, Experimental measurements and theoretical predictions for the MOCVD of gallium arsenide using a barrel-type reactor 102 (1990) 635
Dilawari, A.H. and J. Szekely, A mathematical representation of a modified stagnation flow reactor for MOCVD applications 108 (1991) 491
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Ditzenberger, J.A., see Chiu 107 (1991) 1051
Djafari Rouhani, M., M. Laroussi, A. Amrani and D. Estève, Simulation of GaAs/CdTe heteroepitaxial growth 101 (1990) 122
Djinović, Z., Z. Djurić, Z. Jaksić, F. Kermendi and R. Roknić, Isothermal vapor phase epitaxy of (Hg,Cd)Te from Te-rich $Hg_{1-y}Te_y$ source 108 (1991) 710
Djurić, Z., see Djinović 108 (1991) 710
Dobaczewski, L., E. Janik and G. Karczewski, Deep levels governing the transport mechanism in p–n HgMnTe diodes 101 (1990) 841
Dobročka, E. and J. Sládek, Thermal stress analysis in horizontal Bridgman grown crystals 104 (1990) 419
Dobročka, E., The effect of growth orientation on the resolved shear stresses for horizontal Bridgman grown GaAs crystals 104 (1990) 428
Dobrovinskaya, E.R., L.A. Litvinov and V.V. Pischik, Effects of scattering centers and absorbing coatings on the structure of shaped sapphire 104 (1990) 154
Dobrovinskaya, E.R., L.A. Litvinov and V.V. Pischik, Structure of shaped sapphire grown from multicapillary dies 104 (1990) 165
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Döll, G., M.Ch. Lux-Steiner, Ch. Kloc, J.R. Baumann and E. Bucher, Chemical vapour

transport and structural characterization of layered $MnIn_2Se_4$ single crystals 104 (1990) 593
Döll, G., see Kloc 106 (1990) 635
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Dormans, G.J.M., OMCVD of transition metals and their silicides using metallocenes and (di)silane or silicon tetrabromide 108 (1991) 806
Dörnfeld, C., G. Noll, H. Schwab, J.M. Hvam, Ch. Weber, R. Renner, E.O. Göbel, A. Reznitsky, V. Lyssenko, S.A. Pendjur, O.N. Talensky and C. Klingshirn, Picosecond transient gratings in $CdS_{1-x}Se_x$ mixed crystals 101 (1990) 678
Dosho, S., see Takemura 101 (1990) 81
Dosluoglu, T., U. Sudarsan and R. Solanki, Relationship between gas flows and film composition in organometallic vapor phase epitaxy of $In_{1-x}Ga_xAs$ 106 (1990) 643
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Draeger, N.A., Codeposition of aluminum oxide and silicon oxide on a single crystal tungsten surface 102 (1990) 908
Draïdia, N., R. Azoulay, L. Dugrand, A.C. Papadopoulo, Y. Gao, B. Sermage, P. Ossart and J. Meddeb, Optical quality improvement of MOVPE grown GaAlAs/GaAs double heterostructures on silicon substrates 107 (1991) 483
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Dreyhsig, J., U. Stutenbäumer, H.-E. Gumlich and J.W. Allen, Excited state absorption (ESA) of Mn in ZnS and ZnSe 101 (1990) 443
Druilhe, R., F. Desjonquères, A. Katty, A. Tromson-Carli, D. Lorans, L. Svob, A. Heurtel, Y. Marfaing and R. Triboulet, MOVPE growth and characterization of $Hg_{0.7}Cd_{0.3}Te$ layers 101 (1990) 73
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Eichler, H.J., V. Glaw, A. Kummrow, V. Penschke and A. Wahi, Optically bistable thin film devices using wide-gap II–VI compounds 101 (1990) 695
Eidelman, N., W.E. Brown and J.L. Meyer, The effect of pyrophosphate concentrations on calcium phosphate growth on well-crystallized octacalcium phosphate and hydroxyapatite seed crystals 108 (1991) 385
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Fedotov, A., B. Evtody, Ju. Iliashuk, E. Katz and L. Poljak, Grain boundary structure and electrical activity in shaped silicon 104 (1990) 186
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Feigelson, R.S., see Lu 102 (1990) 807
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Fewcett, T.J. and M.R. Brozel, A quantitative light scattering tomography technique for measuring microprecipitate concentrations in GaAs and InP 103 (1990) 78
Figueras, A., S. Garelik, R. Rodríguez-Cle-

mente, B. Armas, C. Combescure and C. Dupuy, A morphological and structural study of SiC layers obtained by LPCVD using tetramethylsilane 110 (1991) 528
Figueroa, J.M., F. Sánchez-Sinencio, J.G. Mendoza-Alvarez, O. Zelaya, G. Contreras-Puente and A. Díaz-Góngora, Photoluminescence spectra and carrier mobilities in polycrystalline films of CdTe 106 (1990) 651
Filippozzi, J.L., F. Therez, D. Estève, M. Fallahi, D. Kendil, M. Da Silva, M. Barbe and G. Cohen-Solal, Integration of CdTe interdigitated photoconductor with an Al GaAs field-effect transistor 101 (1990) 1013
Fillard, J.P., Investigations of oxygen precipitates in Czochralski silicon wafers by using infrared tomography 103 (1990) 71
Fillard, J.P., P.C. Montgomery, P. Gall, M. Castagné and J. Bonnafé, High resolution and sensitivity infrared tomography 103 (1990) 109
Fillard, J.P., P.C. Montgomery, P. Gall, J. Bonnafé and M. Castagné, Submicron optical sectioning microscopy: a particular inverse problem solution adapted to epilayer defect analysis 103 (1990) 120
Filonov, K.N., see Brantov 104 (1990) 98
Finders, J., J. Geurts, A. Kohl, M. Weyers, B. Opitz, O. Kayser and P. Balk, Composition of selectively grown $In_xGa_{1-x}As$ structures from locally resolved Raman spectroscopy 107 (1991) 151
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Fitting, H.-J., A. von Czarnowski and G.O. Müller, Ballistic transport in alkaline earth sulfides 101 (1990) 876
Flachet, J.C., see Leveque 101 (1990) 364
Flat, A., Silicon incorporation anomaly in LEC grown GaAs 109 (1991) 224
Florez, L.T., see Colas 107 (1991) 47
Fluegel, B., M. Joffre, S.H. Park, R. Morgan, Y.Z. Hu, M. Lindberg, S.W. Koch, D. Hulin, A. Migus, A. Antonetti and N. Peyghambarian, Ultrafast optical nonlinearities in II–VI compounds 101 (1990) 643
Fontecilla-Camps, J.-C., see Roussel 106 (1990) 405
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Foord, J.S., A.J. Murrell, D. O'Hare, N.K. Singh, A.T.S. Wee and T.J. Whitaker, Studies of the surface reactivity of novel hydride adduct precursors for CBE growth of III–V compounds 107 (1991) 1040
Fornuto, G., see Chen 102 (1990) 477
Fotiadis, D.I., S. Kieda and K.F. Jensen, Transport phenomena in vertical reactors for metalorganic vapor phase epitaxy. I. Effects of heat transfer characteristics, reactor geometry, and operating conditions 102 (1990) 441
Fotiadis, D.I. and K.F. Jensen, Thermophoresis of solid particles in horizontal chemical vapor deposition reactors 102 (1990) 743
Fotiadis, D.I., see Giapis 104 (1990) 629
Fotiadis, D.I., see Jensen 107 (1991) 1
Foucaran, A., see Achargui 107 (1991) 410
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Fourcade, R., see Bougnot 107 (1991) 502
Fox, B.A. and W.A. Jesser, Critical thickness in epitaxial GaAsP: comparison of theory and experiment 109 (1991) 252
Fox, B.A., see Black 109 (1991) 241
Fox, D.K. and R. Mazelsky, Impurities: curse and blessing for crystals growers 106 (1990) 1
Foxon, C.T., see Gibson 105 (1990) 81
Foxon, C.T., Understanding growth mechanisms using metalorganic sources 105 (1990) 87
Fraas, L.M., E. Malocsay, V. Sundaram, R.W. Baird, B.Y. Mao and G.Y. Lee, High throughput vacuum chemical epitaxy 105 (1990) 35
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Fratello, V.J. and C.D. Brandle, Thermophysical properties of a $LiCaAlF_6$ melt 109 (1991) 334
Fraundorf, G.K. and L. Shive, Transmission electron microscope study of quartz crucibles used in growth of Czochralski silicon 102 (1990) 157
Frazier, D.O., B.R. Facemire, B.H. Loo, D. Burns and D.B. Thiessen, Solidification behavior of impurity-doped succinonitrile solutions in high-surface area, low-bulk volume containers 106 (1990) 101
Freitas, Jr., J.A., see Bishop 106 (1990) 38
French, C.L., A.T.S. Wee, J.S. Foord and G.J. Davies, Mechanistic aspects relating to the growth of $Ga_xIn_{1-x}As$ by CBE 107 (1991) 1038
Frese, V., G.K. Regel, H. Hardtdegen, A. Brauers, P. Balk, M. Hostalek, M. Lokai and L. Pohl, Coordinatively saturated Ga compounds – a new type of group III precursor for the MOCVD of GaAs 102 (1990) 290
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Fuchs, F., A. Lusson, P. Koidl and R. Triboulet, Fourier transform infrared photoluminescence of $Hg_{1-x}Cd_xTe$ 101 (1990) 722
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Fujii, T., M. Sugawara, S. Yamazaki and K. Nakajima, Macroscopic mechanism of group V interdiffusion in undoped InGaAs/InP quantum wells grown by MOVPE 105 (1990) 348
Fujii, T., H. Ando, A. Sandhu, H. Ishikawa and Y. Sugiyama, Gas-source MBE growth and n-type doping of AlGaAs using TEG, TEA, AsH_3 and Si_2H_6 107 (1991) 1030
Fujii, T., Y. Nagano and J. Shirafuji, Growth by self-flux method and post-annealing effect of $Bi_2Sr_2Ca_1Cu_2O_x$ single crystals 110 (1991) 994
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Fujita, K., Y. Shiba and K. Asai, MOCVD growth of GaAs on Si using (Al,In)GaAs/GaAs buffer layer 107 (1991) 473
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Fujita, Sz., A. Tanabe, T. Kinoshita and Sg. Fujita, Luminescence and electrical properties of ZnSe grown by photo-assisted OMVPE 101 (1990) 48
Fujita, Sz., N. Yoshimura, Y.-H. Wu and Sg. Fujita, Surface reconstruction and stabilization in MOMBE of ZnSe revealed by in-situ RHEED monitoring 101 (1990) 78
Fujita, Sz., see Hirata 104 (1990) 521
Fujita, Sz., S. Maruo, H. Ishio, P.A. Murawala and Sg. Fujita, Surface photochemical reactions for alkyl group elimination from precursors in OMVPE 107 (1991) 644
Fujita, Sz., S. Hayashi, M. Funato, T. Yoshie and Sg. Fujita, Properties of $Zn_{1-x}Cd_xS$ ternary and $Zn_{1-x}Cd_xS_{1-y}Se_y$ quaternary thin films on GaAs grown by OMVPE 107 (1991) 674
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Furuhata, N., H. Shimawaki and A. Okamoto, Selective growth of p^+-GaAs by metalorganic molecular beam epitaxy 107 (1991) 1049

Gadkari, S.C., K.P. Muthe, K.D. Singh, S.C. Sabharwal and M.K. Gupta, Growth of single crystals in $Bi_2(Sr,Ca)_{n+1}Cu_nO_x$ system 102 (1990) 685
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Gao Hongkai, Yun Feng, Zhang Jikang, Hou Xun and Gong Ping, Investigation of MOCVD growth of $Al_xGa_{1-x}As$/GaAs and $Al_xGa_{1-x}As$/GaAs/$Al_xGa_{1-x}As$/GaAs multilayer structures with high Al content 107 (1991) 428
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Garandet, J.P., T. Duffar and J.J. Favier, Vertical gradient freeze growth of ternary GaSb–InSb crystals 106 (1990) 426
Garandet, J.P., T. Duffar and J.J. Favier, On the scaling analysis of the solute boundary layer in idealized growth configurations 106 (1990) 437
Garavito, R.M. and D. Picot, Crystallization of membrane proteins: a minireview 110 (1991) 89
Garber, M.B., S.Ch. Agalarov, I.A. Eliseikina, S.E. Sedelnikova, S.V. Tishchenko, V.A. Shirokov, M.M. Yusupov, L.S. Reshetnikova, S.D. Trakhanov, M.A. Tukalo and A.D. Yaremchuk, Purification and crystallization of components of the protein-synthesizing system from *Thermus thermophilus* 110 (1991) 228
Garbinski, P.A., see Yang 105 (1990) 162
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Gardeniers, J.G.E., M.M.W. Mooren, M.H.J.M. de Croon and L.J. Gilling, The influence of the chlorine–hydrogen ratio in the gas phase on the stability of the {113} faces of silicon in Si–H–Cl CVD 102 (1990) 233
Gardeniers, J.G.E., L.J. Giling, F. de Jong and J.P. van der Eerden, A theoretical study of adsorption equilibria in silicon CVD 104 (1990) 727
Gardeniers, J.G.E., C.H. Klein Douwel and L.J. Giling, Reduced pressure silicon CVD on hemispherical substrates 108 (1991) 319
Garelik, S., see Figueras 110 (1991) 528
Garini, Y., E. Cohen, A. Ron and H. Shtrikman, Exciton states and LO-phonon resonant Raman scattering in CdTe/ZnTe superlattices 101 (1990) 783
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Genzel, C., P. Gille, I. Hähnert, F.M. Kiessling and P. Rudolph, Structural perfection of $Hg_{1-x}Cd_xTe$ grown by THM 101 (1990) 232
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Giapis, K.P. and K.F. Jensen, Effect of operating conditions and precursors on optoelectronic properties of OMVPE grown ZnSe 101 (1990) 111
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MOCVD of ZnSe: modelling and experimental results for growth from dimethylzinc and diethylselenide 104 (1990) 629
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Goessens, C., D. Schryvers, J. Van Landuyt, S. Amelinckx, A. Verbeeck and R. De Keyzer, Characterization of crystal defects in mixed tabular silver halide grains by conventional transmission electron microscopy and X-ray diffractometry 110 (1991) 930
Goetz, G., A. Krost and H.-J. Schulz, $Cr^{2+}(d^4)$ infrared emission in CdS and CdSe 101 (1990) 414
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Gouzerh, P., F. Robert, J. Gouzerh and H. Makram, The effect of the oxygen pressure on the growth of single crystals of $YBa_2Cu_3O_{7-x}$ and $Y_{0.8}Ba_{1.2}Cu_{0.15}Pt_{0.9}O_6$ 102 (1990) 1059
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Granger, R., A. Lasbley, A. Seyni, S. Rolland and R. Triboulet, Study of p-to-n-type conversion in bulk $Hg_{1-x}Zn_xTe$ near $x = 0.15$ 101 (1990) 241
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Hahn, S., K. Kugimiya, M. Yamashita, P.R. Blaustein and K. Takahashi, Characterization of mirror-like wafer surfaces using the magic mirror method 103 (1990) 423
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Haisma, J., J.L.C. Daams, A.F. de Jong, B.H. Koek, J.W.F. Maes, D. Mateika, J.A. Pistorius and P.J. Roksnoer, Lattice-constant-adaptable crystallographics. III. Heteroepitaxial phenomena of semiconductors on garnets; an experimental verification 102 (1990) 1014
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Heimbrodt, W., O. Goede, Th. Köpp, R. Enderlein, M. Pessa and J. Lilja, Optical study of ZnSe and (Zn,Mn)Se MBE layers on GaAs 101 (1990) 705
Heimbrodt, W., C. Benecke, O. Goede and H.-E. Gumlich, Optical study of the antiferromagnetic phase transition in (Cd, Mn)S at highest Mn concentration 101 (1990) 911
Heime, K., see Guimarães 107 (1991) 434
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Hennig, D., M. Hanke and A. Kaschte, Tight binding theory for deep-level native point defects in $Hg_{1-x}Cd_xTe$ 101 (1990) 355
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Hibiya, T., S. Imoto, T. Satoh, Y. Nakabayashi and M. Sakonjyu, Single crystal growth of $Pb_2YBa_2Cu_3O_8$ and $YBa_2Cu_3O_{1-x}$ from $PbO–B_2O_3$ melts 102 (1990) 862
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Hirata, H. and K. Hoshikawa, Oxygen solubility and its temperature dependence in a silicon melt in equilibrium with solid silica 106 (1990) 657
Hirata, S., Sz. Fujita, Sg. Fujita and M. Isemura, OMVPE growth of ZnSe and ZnS_xSe_{1-x} using methylselenol as a selenium source 104 (1990) 521
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Hiruma, K., T. Haga and M. Miyazaki, Surface migration and reaction mechanism during selective growth of GaAs and

AlAs by metalorganic chemical vapor deposition 102 (1990) 717
Hiruma, K., T. Haga, T. Usagawa and A. Ihara, Low contact-resistance GaAs/AlGaAs regrowth interfaces and compositional grading layer formation during growth by metalorganic vapor phase epitaxy 107 (1991) 440
Hjellming, L.N., A thermal model for Czochralski silicon crystal growth with an axial magnetic field 104 (1990) 327
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Hoffmann, A. and U. Scherz, Jahn–Teller effect and zero-phonon line isotope shifts of transition metals in II–VI compounds 101 (1990) 385
Hoffmann, A., I. Broser, P. Thurian and R. Heitz, Fine structure of the Cu^{2+} centre in CdS 101 (1990) 532
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Höschl, P., P. Moravec, V. Prosser, R. Kužel, R. Grill, J. Franc, E. Belas and Yu.M. Ivanov, Galvanomagnetic properties of p-CdTe and p-$Hg_{1-x}Cd_xTe$ 101 (1990) 822
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Itoh, H., T. Nakamura, H. Iwahara and H. Sakamato, Observations of growth process of chemically vapor deposited diamond single crystal 108 (1991) 647
Itoh, K., F. Marumo and Y. Kuwano, β-Barium borate single crystal grown by a direct Czochralski method 106 (1990) 728
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Jantsch, W. and G. Hendorfer, Characterization of deep levels in CdTe by photo-EPR and related techniques 101 (1990) 404
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Jaros, M., A. Zoryk, A.W. Beavis and I. Morrison, Electronic structure, effective masses and non-linear optical response in $Hg_{1-x}Cd_xTe$–$Hg_{1-y}Cd_yTe$ and $Hg_{1-x}Cd_xTe$–$Cd_{1-y}Zn_yTe$ superlattices 101 (1990) 559
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Jones, A.C., S.A. Rushworth, D.A. Bohling and G.T. Muhr, Growth of $Al_xGa_{1-x}As$ by reduced pressure MOVPE using trimethylamine alane (E) 108 (1991) 439
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Karam, N.H., A. Mastrovito, V. Haven, K. Ismail, S. Pennycook and H.I. Smith, Patterning and overgrowth of nanostructure quantum well wire arrays by LP-MOVPE 107 (1991) 591
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Keizer, L.C., X. Tang, R.Z.C. van Meerten and L.J. Giling, Doping of gallium arsenide in MOCVD: equilibrium calculations 102 (1990) 667
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Kibbler, A.E., S.R. Kurtz and J.M. Olson, Carbon doping and etching of MOCVD-grown GaAs, InP, and related ternaries using CCl_4 109 (1991) 258
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Kisker, D.W., P.H. Fuoss, S. Brennan, G. Renaud, K.L. Tokuda and J.L. Kahn, In situ characterization of organometallic growth of ZnSe using grazing incidence X-ray scattering 101 (1990) 42
Kitagawa, M., Y. Tomomura, K. Nakanishi, A. Suzuki and S. Nakajima, Photo-assisted homoepitaxial growth of ZnS by molecular beam epitaxy 101 (1990) 52
Kitamura, M., Precipitation mechanism of polymorphous clathrate crystals of Ni-complex at high concentrations of 1-methylnaphthalene 102 (1990) 255
Kitano, M., T. Hamabe, S. Maeda and T. Okabe, Growth of large tetrapod-like ZnO crystals. I. Experimental considerations on kinetics of growth 102 (1990) 965
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Knight, D.G. and W. Benyon, Method for reliable liquid phase epitaxial growth of semi-insulating InP doped with Ti and Zn 102 (1990) 249
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Kobayashi, N., Oxygen transport under an axial magnetic field in Czochralski silicon growth 108 (1991) 240
Kobayashi, R., H. Yamaguchi, Y. Jin and F. Hasegawa, Difference of reaction between AsH_3 and arsenic vapor from As metal in vapor phase epitaxy of GaAs 102 (1990) 471
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Kubo and H. Fujiwara, Turbulent heat transfer through the melt in silicon Czochralski growth 109 (1991) 149
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Koide, Y., S. Zaima, N. Ohshima and Y. Yasuda, Growth processes in the initial stages of deposition of Ge films on (100)Si surfaces by GeH_4 source molecular beam epitaxy (E) 104 (1990) 871
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Komatsu, S. and Y. Moriyoshi, Growth forms of β-rhombohedral boron whiskers and platelets prepared in a low-pressure B_2H_6 + He plasma in terms of periodic bond chain method 108 (1991) 63
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Komeno, J., H. Tanaka, N. Tomesakai, H. Itoh, T. Ohori, M. Takikawa, M. Suzuki and K. Kasai, Recent progress in MOVPE for HEMT LSIs 105 (1990) 30
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Konagai, M., T. Yamada, T. Akatsuka, S. Nozaki, R. Miyake, K. Saito, T. Fukamachi, E. Tokumitsu and K. Takahashi, Metallic p-type GaAs and InGaAs grown by MOMBE 105 (1990) 359
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Kondo, M., K. Domen, C. Anayama, T. Tanahashi and K. Nakajima, MOVPE growth and optical properties of Al GaInP/GaInP strained single quantum well structures 107 (1991) 578
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Korte, L., R. Treichler, M. Schreiber, Ch. Tanner, G. Kristen, C. Hanke and G. Weimann, Interaction of the dopants Mg and Si in $Al_xGa_{1-x}As$/GaAs heterolayers (MOVPE): application to DQW laser structures 107 (1991) 779
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Krause, R., A. Klimakow, F.M. Kiessling, A. Polity, P. Gille and M. Schenk, Study of Hg vacancies in (Hg,Cd)Te after THM growth and post-growth annealing by positron annihilation 101 (1990) 512

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Kresse, F., G.G. Baumann, O. Jäntsch and K. Haberger, Liquid phase epitaxy of silicon at low temperatures 104 (1990) 744

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Kudlek, G., N. Presser, J. Gutowski, S. Durbin, D. Menke, M. Kobayashi and R.L. Gunshor, High-density luminescence and excitation spectroscopy of MBE-grown ZnSe/GaAs epilayers 101 (1990) 667

Kuech, T.F., M.S. Goorsky, M.A. Tischler, A. Palevski, P. Solomon, R. Potemski, C.S. Tsai, J.A. Lebens and K.J. Vahala, Selective epitaxy of GaAs, $Al_xGa_{1-x}As$, and $In_xGa_{1-x}As$ 107 (1991) 116

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Lakrimi, M., N.J. Mason, R.J. Nicholas, G.B. Stringfellow, G. Summers and P.J. Walker, Absorption characteristics of GaSb/InAs and InSb/InAs SLSs grown on (111) GaAs by MOVPE 107 (1991) 518
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Lambrecht, A., N. Herres, B. Spanger, S. Kuhn, H. Böttner, M. Tacke and J. Evers, Molecular beam epitaxy of $Pb_{1-x}Sr_xSe$ for the use in IR devices 108 (1991) 301
Lambropoulos, J.C., High temperature inelastic deformation during shaped crystal growth from the melt 104 (1990) 1
Lan, C.W. and S. Kou, Thermocapillary flow and melt/solid interfaces in floating-zone crystal growth under microgravity 102 (1990) 1043
Lan, C.W., Y.J. Kim and S. Kou, A half-zone study of Marangoni convection in floating-zone crystal growth under microgravity 104 (1990) 801
Lan, C.W. and S. Kou, Floating-zone crystal growth with a heated ring covering the melt surface 108 (1991) 1
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Laudise, R.A., W.A. Sunder, R.F. Belt and G. Gashurov, Solubility and $P-V-T$ relations and the growth of potassium titanyl phosphate 102 (1990) 427
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Mateika, D., H. Kohler, H. Laudan and E. Völkel, Mixed-perovskite substrates for high-T_c superconductors 109 (1991) 447
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Matsumura, N., T. Fukada and J. Saraie, Laser irradiation during MBE growth of ZnS_xSe_{1-x}: a new growth parameter 101 (1990) 61
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Maxey, C.D., P. Capper, P.A.C. Whiffin, B.C. Easton, I. Gale, J.B. Clegg, A. Harker and C.L. Jones, Extrinsic doping at low concentrations for $Cd_xHg_{1-x}Te$ layers grown by MOVPE 101 (1990) 300
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Milchev, A. and R. Lacmann, On the nucleation theory of electrochemical alloy formation. I. Overvoltage dependence of the stationary nucleation rate 110 (1991) 919
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Morishita, Y., M. Imaizumi, M. Gotoda, S. Maruno, Y. Nomura and H. Ogata, Electrical and optical properties of silicon doped InP grown by gas source MBE 104 (1990) 457

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Mullin, J.B., R. Holland, G.W. Blackmore, J.A. Roberts, I.G. Gale, F. Grainger and J.B. Clegg, Analysis of cadmium mercury telluride and related materials 106 (1990) 127

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D.A. Andrews, Surface studies of the thermal decomposition of triethylgallium on GaAs (100) 105 (1990) 199
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Naganuma, M., M. Notomi, H. Iwamura, M. Okamoto, T. Nishida and T. Tamamura, InGaAs/InP quantum well wires fabricated by GSMBE, MOCVD, and selective chemical etching techniques 105 (1990) 254
Nagata, K., Y. Iimura, Y. Aoyagi and S. Namba, Laser assisted chemical beam epitaxy 105 (1990) 52
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Nakajima, M., A. Takamori, T. Yokotsuka, K. Uchiyama and T. Abe, Study of AlInP and GaInP grown by gas source molecular beam epitaxy (GSMBE) 105 (1990) 116
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Nishikawa, Y., S. Naritsuka, M. Ishikawa, M. Suzuki and Y. Kokubun, MOCVD growth of InGaAlP using ethyldimethylindium as an In source and application to visible-region lasers 104 (1990) 245
Nishikawa, Y., H. Sugawara, M. Ishikawa and Y. Kokubun, Effects of V/III ratio on Zn electrical activity in Zn-doped In GaAlP grown by metalorganic chemical vapor deposition 108 (1991) 728
Nishimura, K., see Yokota 103 (1990) 65
Nishimura, T., K. Kadoiwa, N. Hayafuji, M. Miyashita, K. Mitsui, H. Kumabe and T. Murotani, Surface morphology improvement of GaAs-on-Si using a two-reactor MOCVD system and an AlAs/GaAs low temperature buffer layer: an approach to crack-free GaAs-on-Si 107 (1991) 468
Nishino, H., see Ueda 104 (1990) 695
Nishio, J., Transport restriction effect for gaseous components on the carbon content of LEC GaAs 108 (1991) 150
Nishiyama, S., C. Takenaka, T. Kusunoki, T. Fujii and K. Nakajima, LPE growth of InP and InGaAs on MQW layers below 500 °C 104 (1990) 809
Nissenbaum, J., see Hermon 109 (1991) 376
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Noll, G., U. Siegner, E.O. Göbel, H. Schwab, R. Renner and C. Klingshirn, Optical dephasing in CdSSe mixed crystals studied by coherent transient grating experiments 101 (1990) 731
Nomura, Y., see Morishita 104 (1990) 457
Nomura, Y., see Morishita 105 (1990) 221
Nonaka, K., see Yoshimura 102 (1990) 1035
Nordell, N., B. Willén, C.-O.A. Olsson, U. Westergren and G. Landgren, Growth and performance of AlGaAs/GaAs heterostructure bipolar transistors 107 (1991) 909
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Norton, M.G. and C.B. Carter, The nucleation and heteroepitactic growth of $YBa_2Cu_3O_{7-\delta}$ thin films on MgO 110 (1991) 641
Norton, M.L., see Tissue 109 (1991) 323
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Nouruzi-Khorasani, A., I.P. Jones, P.S. Dobson, Y. Etem, D.J. Williams, M.G. Astles, C. Ard and G. Coates, A cross-sectional TEM study of MOVPE grown CdHgTe 102 (1990) 819
Nouruzi-Khorasani, A., M.A. Lunn, I.P. Jones, P.S. Dobson, D.J. Williams and M.G. Astles, Surface damage of CdTe by mechanical polishing investigated by cross-sectional TEM 102 (1990) 1069
Novák, J., S. Hasenöhrl, M. Kuliffayová and J. Oswald, Gettering properties of PrO_2 in $In_{0.53}Ga_{0.47}As$ LPE growth 110 (1991) 862
Nowitzki, A., see Laube 107 (1991) 156
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Nyce, T.A. and F. Rosenberger, Growth of protein crystals suspended in a closed loop thermosyphon 110 (1991) 52
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O'Donnell, K.P., P.J. Parbrook, B. Henderson, C. Trager-Cowan, X. Chen, F. Yang, M.P. Halsall, P.J. Wright and B. Cockayne, Photoluminescence of wide bandgap II–VI superlattices 101 (1990) 554
O'Donnell, K.P., see Parbrook 106 (1990) 503
Oesten, R. and H. Böhm, Flux growth of melilite single crystals 102 (1990) 919
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Ohki, Y. and Y. Hiratani, Mass spectrometric study of the reaction of trimethylgallium and GaAs 105 (1990) 77
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Ohno, T. and T. Taguchi, The effects of photo-assisted MOCVD on the doping of Na acceptors into ZnS epitaxial layers 107 (1991) 649
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Ohori, T., see Takikawa 107 (1991) 942
Ohsaka, K., E.H. Trinh and M.E. Glicksman, Undercooling of acoustically levitated molten drops 106 (1990) 191
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Ohshita, Y., Theoretical studies on CH_2 adsorption process in β-SiC vapor phase epitaxial growth 110 (1991) 516
Ohta, K., T. Kojima and T. Nakagawa, Phase diagrams of RHEED intensity oscillations accompanying the incorporation of As into very thin Al films; possible melting point lowering of thin Al film 110 (1991) 509
Ohta, S., S. Kobayashi, F. Kaneko and K. Kashiro, Growth of CdS/ZnS superlattices at low temperature by atomic layer epitaxy 106 (1990) 166
Ohtsuka, K., T. Ohishi, Y. Abe, H. Sugimoto and T. Matsui, High resistivity InP layer grown by low temperature liquid phase epitaxy 106 (1990) 467
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Okabayashi, O., H. Shirotori, H. Sakurazawa, E. Kanda, T. Yokoyama and M. Kawashima, Evaluation of directly bonded silicon wafer interface by the magic mirror method 103 (1990) 456
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Okabe, T., see Kitano 108 (1991) 277
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Okada, K., S. Komatsu, S. Matsumoto and Y. Moriyoshi, Growth steps and etch pits appearing on {100} planes of diamonds prepared by combustion-flame deposition method 108 (1991) 416
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Okano, Y., T. Fukuda, A. Hirata, N. Takano, T. Tsukada, M. Hozawa and N. Imaishi, Numerical study on Czochralski growth of oxide single crystals 109 (1991) 94
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Okihara, T., A. Kawaguchi, M. Ohara and K. Katayama, Subcell-matched epitaxy of normal long chain compounds on polyethylene. I. On the (110) plane 106 (1990) 318
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Olech, A.Z. and S.A. Hodorowicz, The growth kinetics of urea monocrystals from 1-propanol-aqueous solutions 102 (1990) 562
Olego, D.L. and D. Cammack, Optoelectronic properties of ZnSe–GaAs interfaces: role of interface chemistry and structural defects 101 (1990) 546
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Ono, H., Axial dislocations in LEC-grown In-doped GaAs crystals 102 (1990) 949
Onodera, C. and T. Taguchi, A new 1.47 eV defect-luminescence band in MOCVD-grown CdTe on (100) GaAs 101 (1990) 502
Onuma, K., A. Kasahara, K. Kato, N. Aihara and T. Udagawa, Atmospheric-pressure MOVPE growth of InP using Lewis base monovalent cyclopentadienyl indium 107 (1991) 360
Onuma, K., K. Tsukamoto and I. Sunagawa, Dissolution kinetics of K-alum crystals as judged from the measurements of surface undersaturations 110 (1991) 724
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Ossau, W., T.A. Kuhn and R.N. Bicknell-Tassius, Linear and quadratic Zeeman effects on PAMBE grown CdTe 101 (1990) 135
Ossau, W., S. Fisher and R.N. Bicknell-Tassius, Magneto-excitons in CdTe–(CdMn)Te quantum wells 101 (1990) 905
Ostrogorsky, A.G., Numerical simulation of single crystal growth by submerged heater method 104 (1990) 233
Ostrogorsky, A.G., F. Mosel and M.T. Schmidt, Diffusion-controlled distribution of solute in Sn–1%Bi specimens solidified by the submerged heater method 110 (1991) 950
Oswald, J., see Novák 110 (1991) 862
Otani, S., T. Tanaka and Y. Ishizawa, Automatic crystal growth of refractory metals (Mo, Ta, W) by the float zone technique 106 (1990) 498
Otani, S., T. Tanaka and Y. Ishizawa, Preparation of $(La_{1-x}Ce_x)B_6$ single crystals by the floating zone method 108 (1991) 425
Otoki, T., M. Watanabe, T. Inada and S. Kuma, Investigation of changes of As precipitates in semi-insulating GaAs crystals at several temperatures by infrared light scattering tomography 103 (1990) 85
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Ouadjaout, D., Y. Marfaing, A. Lusson and A. Heurtel, Density of states model and photoluminescence spectra of localized excitons in ZnHgTe and CdHgTe alloys 101 (1990) 709
Ougazzaden, A., J.-D. Ganière, Y. Gao, E.V.K. Rao, B. Sermage, C. Kazmierski and A. Mircea, Low threshold 1.5 μm SCH-MQW lasers by atmospheric pressure MOVPE and direct comparison of low versus atmospheric pressure MOVPE laser growth 107 (1991) 761
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Owczarek, I. and K. Sangwal, Effect of impurities on the growth of KDP crystals: mechanism of adsorption on (101) faces 102 (1990) 574
Ozasa, K., M. Yuri and H. Matsunami, Temperature dependence of InGaP, InAlP, and AlGaP growth in metalorganic molecular-beam epitaxy 102 (1990) 31
Ozawa, T., Y. Hayakawa and M. Kumagawa, Growth of III–V ternary and quaternary mixed crystals by the rotationary Bridgman method 109 (1991) 212
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Ozoe, H., K. Toh and T. Inoue, Transition mechanism of flow modes in Czochralski convection 110 (1991) 472

Packeiser, G., H. Tews and P. Zwicknagl, High frequency AlGaAs/GaAs heterojunction bipolar transistors: the role of MOVPE 107 (1991) 883
Pagès, O., M. Renucci, O. Briot, N. Tempier and R.L. Aulombard, Raman characterization of ZnSe/GaAs MOVPE heterostructures 107 (1991) 670
Pain, G.N., N. Bharatula, G.I. Christiansz, M.H. Kibel, M.S. Kwietniak, C. Sandford, T. Warminski, R.S. Dickson, R.S. Rowe, K. McGregor, G.B. Deacon, B.O. West, S.R. Glanvill, D.G. Hay, C.J. Rossouw and A.W. Stevenson, use of MeMn$(CO)_5$ in the low temperature MOCVD growth on Mn containing alloys 101 (1990) 208
Pain, G.N., see Rossouw 106 (1990) 673
Pain, G.N., C. Sandford, G.K.G. Smith, A.W. Stevenson, D. Gao, L.S. Wielunski, S.P. Russo, G.K. Reeves and R. Elliman, Low temperature MOCVD of $Hg_{1-x}Cd_xTe$ on 311, 511, 711 and shaped GaAs 107 (1991) 610
Pain, G.N., C.J. Rossouw, S.R. Glanvill, R.S. Rowe, R.S. Dickson, G.B. Deacon and B.O. West, HRTEM studies of defects

and interdiffusion in $Hg_{1-x-y}Mn_yCd_xTe$ ($0 \leq x, y \leq 1$) grown by low temperature MOCVD 107 (1991) 632

Pajaczkowska, A., O. de Melo, F. Leccabue, C. Pelosi, D. Fiorani, A.M. Testa and E. Paparazzo, CVT growth, and magnetic and electronic properties of $NiGa_2O_4$ single crystals 104 (1990) 498

Pak, K., see Tanako 102 (1990) 341

Pak, K., K. Ashizuka, H. Fukazawa, S. Yamashita, Y. Takano and H. Yonezu, Carbon dopin in GaAs grown by MOVPE with trimethylgallium and triethylarsenic 106 (1990) 715

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Parat, K.K., N.R. Taskar, I.B. Bhat and S.K. Ghandhi, The influence of accumulation of the Hall-effect in n-type $Hg_{1-x}Cd_xTe$ 102 (1990) 413

Parat, K.K., N.R. Taskar, I.B. Bhat and S.K. Ghandhi, Annealing and electrical properties of $Hg_{1-x}Cd_xTe$ grown by OMVPE 106 (1990) 513

Parat, K.K., see Taskar 110 (1991) 692

Parbrook, P.J., see O'Donnell 101 (1990) 554

Parbrook, P.J., see Wright 104 (1990) 601

Parbrook, P.J., P.J. Wright, B. Cockayne, A.G. Cullis, B. Henderson and K.P. O'Donnell, The growth of ZnSe/CdSe and ZnS/CdS strained layer superlattices by MOVPE 106 (1990) 503

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Park, Y.J., C.W. Han, K.B. Shim, S.C. Park, C.B. Kim and S.-K. Min, Growth and characterization of GaAs : In by a new horizontal zone melt technique 104 (1990) 610

Parker, C.A., see Gong 107 (1991) 83

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Parsons, J.D. and L.S. Lichtmann, Temperature-independent unassisted pyrolytic MOCVD growth of cadmium telluride at 290 °C and mercury telluride at 325 °C using dimethylcadmium, methylallyltelluride and dimethylmercury (E) 106 (1990) 745

Pascal, F., see Bougnot 107 (1991) 502

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Paska, Z.F., J.Y. Andersson, L. Lundqvist and C.-O.A. Olsson, Growth and characterization of AlGaAs/GaAs quantum well structures for the fabrication of long wavelength infrared detectors 107 (1991) 845

Patel, D., see Smith 107 (1991) 605

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Paulsson, G., K. Deppert, S. Jeppesen, J. Jönsson, L. Samuelson and P. Schmidt, Reflectance-difference detection of growth oscillations 105 (1990) 312

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Pelcé, P., D. Rochwerger and A. Karma, Oscillatory instability and minimum undercooling criterion in directional solidification 110 (1991) 815

Pelekanos, N., Q. Fu, A.V. Nurmikko, S. Durbin, J. Han, Sungki O, D. Menke, M. Kobayashi and R.L. Gunshor, Spectroscopy in CdTe/MnTe and ZnTe/MnTe single quantum wells; new binary wide gap II–VI heterostructures 101 (1990) 628

Pelleg, J., see Ditchek 102 (1990) 401

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Pemble, M.E., D.S. Buhaenko, S.M. Francis, P.A. Goulding and J.T. Allen, Surface science studies of MOVPE processes: a review of progress 107 (1991) 37

Peña-Sierra, R., J.G. Castro-Zavala and A. Escobosa, Growth of GaAs by MOCVD using a solid arsenic source 107 (1991) 337

Pendjur, S.A., see Dörnfeld 101 (1990) 678

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Pénisson, J.-M. and A. Renou, Structure of an isocahedral palladium particle 102 (1990) 585
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Pet'kov, I.S. and B.S. Red'kin, Stability analysis of movable menisci 104 (1990) 20
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Piekarczyk, W. and W.A. Yarbrough, Application of thermodynamics to the examination of the diamond CVD process. II. A model of diamond deposition process from hydrocarbon–hydrogen mixtures 108 (1991) 583
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Pohl, L., see Scholz 107 (1991) 365
Pohl, U.W. and H.-E. Gumlich, Long range Mn ion pairs and other Mn related centers in ZnS detected by site-selected spectroscopy 101 (1990) 521
Polity, A., see Krause 101 (1990) 512
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Polman, A., S. Roorda, P.A. Stolk and W.C. Sinke, Triggering explosive crystallization of amorphous silicon 108 (1991) 114
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Potts, J.E., H. Cheng, J.M. DePuydt and M.A. Haase, p-Doping of epitaxial ZnSe using group I elements 101 (1990) 425
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Prior, K.A., J.M. Wallace, J.J. Hunter, S.J.A. Adams, M.J.L.S. Haines, M. Saoudi and B.C. Cavenett, Growth of MBE ZnS_xSe_{1-x} using a novel electrochemical sulphur source 101 (1990) 176
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Rakennus, K., K. Tappura, T. Hakkarainen, H. Asonen, R. Laiho, S.J. Rolfe and J.J. Dubowski, Interface effects on electrical properties of high purity InP grown by gas-source molecular beam epitaxy 110 (1991) 910
Ramakrishna Reddy, K.T. and P. Jayarama Reddy, Preparation and properties of laser evaporated $CuGaSe_2$ thin films 108 (1991) 765
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Rao, S.M., A.K. Batra, C. Cao and R.B. Lal, Etch pit study of different crystallographic faces of L-arginine phosphate (LAP) 106 (1990) 481
Rao, S.M., B.H. Loo, N.P. Wang and R.J. Kelley, A new technique for the growth of superconducting $YBa_2Cu_3O_{6+\delta}$ crystals completely separated from flux 110 (1991) 989
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Ravishankar Rao, A. and R. Jain, A classification scheme for visual defects arising in semiconductor wafer inspection 103 (1990) 398
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Richter, W., see Wisser 107 (1991) 111
Riedel, M. and R. Dässler, Pressure-induced nucleation and growth processes in the diamond anvil cell 106 (1990) 695
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Roberts, J.S., C.C. Button, J.P.R. David, A.C. Jones and S.A. Rushworth, MOVPE growth of AlGaAs using trimethylamine alane 104 (1990) 857
Roberts, J.S., K.C. Singh, C.C. Button, J.P.R. David and J. Woodhead, AlGaAs/GaAs p-MODFET materials grown using intrinsic carbon doping 107 (1991) 915
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Rozgonyi, G.A., see Bivas 103 (1990) 200
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Said, M. and M.A. Kanehisa, Excited states of acceptors in CdTe and ZnTe 101 (1990) 488

Saidin, M.K.B., G.J. Russell, A.W. Brinkman and J. Woods, Hall mobility and conductivity in $Zn_xCd_{1-x}S$ mixed crystals 101 (1990) 844

Saito, H., M. Ohishi, A. Watanabe and K. Ohmori, Strain-induced splitting of free exciton band in epitaxially grown ZnSe on GaAs 101 (1990) 727

Saito, H., see Fukui 107 (1991) 231

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Saito, Y., T. Shishido, N. Toyota, K. Ukei, T. Sasaki and T. Fukuda, Crystal growth and properties of $R_2Ba_2CuPtO_8$ (R = Ho, Er, Y), $R_2Ba_3Cu_2PtO_{10}$ and $Ba_4CuPt_2O_9$ 109 (1991) 426

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Sanz-Maudes, J., J. Sangrador and T. Rodriguez, Numerical description of the phase diagram of the Hg–Cd–Te system in the Te-rich corner 102 (1990) 1065

Sanz-Maudes, J., J. Sangrador, T. Rodriguez, A. Pernichi and C. Gonzalez, Numerical simulation of the growth of HgCdTe layers by liquid phase epitaxy from Te-rich solutions: the effect of liquid dimensions and mercury loss 106 (1990) 303

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Scalbert, D., J.A. Gaj, A. Mauger, J. Cernogora, C. Benoit à la Guillaume and

A. Mycielski, Resonant Raman scattering on low energy excited states of Fe^{2+} in $Cd_{1-x}Fe_xSe$ 101 (1990) 940
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Schenk, A., M. Stahl and H.-J. Wünsche, Tunneling current calculated for $Hg_{0.8}Cd_{0.2}Te$ diodes 101 (1990) 350
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Schetzina, J.F., J.W. Han, Y. Lansari, N.C. Giles, Z. Yang, S. Hwang, J.W. Cook, Jr. and N. Otsuka, Modulation-doped HgCd Te quantum well structures and superlattices grown by photoassisted molecular beam epitaxy 101 (1990) 23
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Schmelzer, J., I. Gutzow and R. Pascova, Kinetics of phase segregation in elastic and viscoelastic media 104 (1990) 505
Schmid, D., R.H. Mauch, M. Hofmann, R. Schäffler and H.W. Schock, Highly conductive Ga-doped polycrystalline (Zn, Cd)S films 101 (1990) 1018
Schmid, U., see Christensen 101 (1990) 318
Schmidt, A., M. Müller, J. Grohs, M. Kunz, A. Daunois, V. Kažukauskas, A.K. Kar, H. Bartelt and C. Klingshirn, Thermally induced optical bistability in II–VI semiconductor crystals and thin films 101 (1990) 758
Schmidt, F.A., see Lograsso 110 (1991) 363
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Schmidt, H., J.W. Tomm and K.H. Herrmann, Middle infrared photoluminescence mapping of II–VI semiconductor wafers 101 (1990) 474
Schmidt, M.T., see Ostrogorsky 110 (1991) 950
Schmidt, P., K. Deppert, S. Jeppesen, J. Jönsson, G. Paulsson and L. Samuelson, A compact VCE growth system for in situ studies of epitaxy 105 (1990) 306
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Schmidt, P., K. Deppert and H. Kostial, Silicon spike-doping of GaAs with AP-MOVPE 107 (1991) 259
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Schmidt, T., H. Sitter and K. Lischka, Bulk-like low-temperature photoluminescence from CdTe/GaAs grown by hot-wall epitaxy 101 (1990) 190
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Sunder, Molecular beam epitaxy growth and characterization of GaSb/AlSb strained-layer superlattices on nonvicinal (001) and 111(B) GaSb substrates 102 (1990) 147
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Shen, J.Y. and C. Chatillon, Thermodynamic analysis of molecular beam epitaxy of III–V compounds; application to the $Ga_yIn_{1-y}As$ multilayer epitaxy 106 (1990) 553
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Shibata, N. and A. Katsui, Monolayer epitaxy of ZnSe on GaAs substrates by alternating adsorption of diethylzinc and hydrogenselenide 101 (1990) 91
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Shimoyama, K., Y. Inoue, M. Katoh, H. Gotoh, Y. Suzuki and H. Yajima, A new selective MOVPE regrowth process utilizing in-situ vapor phase etching for optoelectronic integrated circuits 107 (1991) 767
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Sibille, L. and J.K. Baird, Analysis of solvent evaporation rates in the vapor diffusion protein crystal growth experiments from the STS-61C Space Shuttle Mission 110 (1991) 72
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lot, The growth of CMT on GaAs for high quality linear arrays of MWIR and LWIR photodiodes 107 (1991) 605
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Sobiesierski, Z., I.M. Dharmadasa and R.H. Williams, Photoluminescence as a probe of semiconductor surfaces: CdTe and CdS 101 (1990) 599
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Stefani, J.A., J.K. Tien, K.S. Choe and J.P. Wallace, Multifrequency eddy current diagnostics of axial and radial thermal profiles during silicon crystal growth 106 (1990) 611
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Suemitsu, M., F. Hirose, Y. Takakuwa and N. Miyamoto, Growth kinetics in silane gas-source molecular beam epitaxy 105 (1990) 203
Suemitsu, M., F. Hirose and N. Miyamoto, Si and Ge gas-source molecular beam epitaxy (GSMBE) 107 (1991) 1015
Suemune, I., H. Masato, K. Nakanishi, K. Yamada, Y. Kan and M. Yamanishi, Photopumped lasing in ZnSSe/ZnSe multilayer structures up to 210 K 101 (1990) 754
Suemune, I., H. Masato, K. Nakanishi, Y. Kuroda and M. Yamanishi, Doping of nitrogen in ZnSe films: improved doping properties in ZnSe/ZnSSe periodic layered structures grown on GaAs by MOVPE 107 (1991) 679
Suemune, I., K. Hamaoka, A. Kishimoto, T. Koui, Y. Honda and M. Yamanishi, Hydrogen-plasma and photo-effects on MOMBE of GaAs 107 (1991) 1041
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Sugiyama, H. and O. Nittono, Microstructure and lattice distortion of anodized porous silicon layers 103 (1990) 156
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Suzuki, K., see Ueno 102 (1990) 643
Suzuki, M., I. Hide, T. Yokoyama, T. Matsuyama, Y. Hatanaka and Y. Maeda, Growth of polycrystalline silicon sheet by Hoxan cast ribbon process 104 (1990) 102
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Toba, R. and M. Tajima, Surface characterization of semi-insulating GaAs wafers by room temperature photoluminescence mapping 103 (1990) 28

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Turco, F.S., S. Simhony, K. Kash, D.M. Hwang, T.S. Ravi, E. Kapon and M.C. Tamargo, Molecular beam epitaxial growth of GaAs/AlAs and GaAs/Al GaAs quantum wells on sub-micron-period corrugated substrates 104 (1990) 766
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Uchida, T.K., T. Uchida, K. Mise, N. Yokouchi, F. Koyama and K. Iga, CBE growth of GaInAs–InP wafers for surface emitting lasers 107 (1991) 1055
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Ushakov, N.G., Models and algorithms of image processing of local SEM diagnostics 103 (1990) 413
Ushakov, V.V. and A.A. Gippius, 5d Transition and 4f rare earth elements in II–VI semiconductors as luminescent centres and probes in diagnostics of implanted layers 101 (1990) 458
Utsu, T. and S. Akiyama, Growth and applications of Gd_2SiO_5 : Ce scintillators 109 (1991) 385
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Van der Voort, E. and P. Hartman, Morphology of polar $ASO_3 \cdot 6H_2O$ crystals (A = Ni, Co, Mg) and solvent interaction 106 (1990) 622
Van der Voort, E., The theoretical growth form of potassium nitrate from an aqueous solution 110 (1991) 653
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Varnhorst, T., O.F. Shirmer and H. Hesse, Blue coloration of $KNbO_3$ caused by scattering 108 (1991) 429
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Venkatasubramanian, R., M.L. Timmons, J.B. Posthill, B.M. Keyes and R.K. Ahrenkiel, High quality GaAs on Si using $Si_{0.04}Ge_{0.96}$/Ge buffer layers 107 (1991) 489
Venturini, E.L., C.P. Tigges, R.J. Baughman, B. Morosin, J.C. Barbour, M.A. Mitchell and D.S. Ginley, Stoichiometry and irradiation effects in melt grown Tl–Ca–Ba–Cu–O single crystals 109 (1991) 441
Verbeeck, A., see Goessens 110 (1991) 930
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Vesenka, J.P. and Y. Yeh, Defect site nucleation of microbubbles as a source of dynamic light scattering at the growing ice–water interface 108 (1991) 19
Veuhoff, E., H. Baumeister, O. Brandt and R. Treichler, Mg incorporation process during LP-MOVPE of InP, GaInAs and GaInAsP 105 (1990) 353
Viale, D., G. Weber and B. Gillot, Growth of Cu_3Si from CuCl vapor deposition on Si(100) oriented wafers 102 (1990) 269
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Visser, E.P., C.A.M. Govers and L.J. Giling, Measurement of gas-switching related diffusion phenomena in horizontal MOCVD reactors using biacetyl luminescence 102 (1990) 529
Vitrià, J. and J.J. Villanueva, Mathematical morphology applied to integrated circuit inspection 103 (1990) 407
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Vogel, E.E., M.A. de Orúe, J. Rivera-Iratchet and J.E. Morales, Jahn–Teller effect of $CdS:Fe^{2+}$ and $CdSe:Fe^{2+}$ 101 (1990) 470
Vogels, L.J.P., P. Bennema, M.H.J. Hottenhuis and M.C. Elwenspoek, On the morphology of ammonium nitrate (III): theory and observation 108 (1991) 733
Vogels, L.J.P., M.A. Verheijen and P. Bennema, On the morphology of β-K_2SO_4 type structures: theory and observation 110 (1991) 604
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Wagner, G. and R. Linhardt, Liquid–liquid diffusion profiles in microgravity experiments, and crystal growth of the membrane protein bacteriorhodopsin 110 (1991) 114
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Wang Qiwei and Jia Shouquan, Theoretical estimation of the crystal growth driving force during slow cooling 102 (1990) 678
Wang, T.H., T.F. Ciszek and T. Schuyler, Charge carrier recombination centers in high-purity, dislocation-free, float-zoned silicon due to growth-induced microdefects 109 (1991) 155
Wang, T.Y., A.W. Kimball, G.S. Chen, D. Birkedal and G.B. Stringfellow, GaInP/AlGaInP strained quantum wells grown using atmospheric pressure organometallic vapor phase epitaxy 109 (1991) 285
Wang, Y., P. Bennema and P. van der Linden, Double crucible method for the growth of large superconducting YBCO single crystals 106 (1990) 483
Wang, Y., L.W.M. Schreurs, P. van der Linden, Y. Li and P. Bennema, A new procedure for the isolation of large YBCO superconducting single crystals 106 (1990) 487
Wang Yaoshui, Zheng Manna, P. Bennema, Zhu Rui, Ye Guifen, Liu Xiangyang and W.J.P. van Enckevort, The occurrence of scattering centres and dislocations in KDP crystals 108 (1991) 821
Wang, Z.G., C.J. Li, S.K. Wan and L.Y. Lin, Spatial distributions of impurities and defects in Te- and Si-doped GaAs grown in a reduced gravity environment 103 (1990) 38
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Weyher, J.L., C. Frigeri and P.J. van der Wel, Complementary DSL, EBIC and PL study of grown-in defects in Si-doped GaAs crystals grown under Ga- and As-rich conditions by LEC method 103 (1990) 46
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Weyher, J.L., P. Gall, G. Frigerio and L. Zanotti, Study of decoration microdefects in LEC-grown Si-doped GaAs crystals by selective photoetching and laser scattering tomography 106 (1990) 175
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Wilcox, W.R., see Caram 106 (1990) 294
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Winnacker, A. and F.X. Zach, The distribution of the deep donor EL2 and the net acceptor concentration in semi-insulating GaAs 103 (1990) 275
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Wisser, J., P. Czuprin, D. Grundmann, P. Balk, M. Waschbüsch, R. Lückerath and W. Richter, GaAs epitaxy using alternate pulses in a standard LP-MOVPE reactor 107 (1991) 111
Witkamp, G.J., J.P. van der Eerden and G.M. van Rosmalen, Growth of gypsum. I. Kinetics 102 (1990) 281
Witkamp, G.J. and G.M. van Rosmalen, Growth of gypsum. II. Incorporation of cadmium 108 (1991) 89
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Woelk, W., M.E. Sherwin, G.O. Munns and G.I. Haddad, Technical aspects of In GaAs MOMBE – shutter action, system drift, and material quality 110 (1991) 452
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Wright, P.J., B. Cockayne, P.J. Parbrook, A.C. Jones, P. O'Brien and J.R. Walsh, MOCVD layer growth of ZnSe and ZnS/ZnSe multiple layers using nitrogen containing adducts of dimethylzinc 104 (1990) 601
Wright, P.J., see Parbrook 106 (1990) 503
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Wright, P.J., B. Cockayne, P.J. Parbrook, P.E. Oliver and A.C. Jones, Control of prereaction in the metalorganic chemical vapour deposition of zinc- and cadmium-based chalcogenides 108 (1991) 525
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Wu Fengmei, Shi Yi and Wang Changhe, Investigation of neutron radiation defects in silicon by high discriminability deep level transient spectroscopy (HDDLTS) 103 (1990) 282
Wu, J., P.G. Mo, G.Y. Wang, S. Benakki, E. Christoffel, A. Goltzene, C. Schwab, J.R. Wang and C.H. Lee, Influence of In-doping on dislocations in liquid encapsulated Czochralski (LEC) grown gallium arsenide 102 (1990) 701
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Wu, O.K., J.N. Schulman and G.S. Kamath, HgTe/HgCdTe superlattices: growth, electrical and optical properties 101 (1990) 96
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Wynblatt, P., J.J. Métois and J.C. Heyraud, Modeling the growth of dendrite-like gold islands on graphite substrates 102 (1990) 618

Xiao, R.F., J.I.D. Alexander and F. Rosenberger, Simulation of surface morphologies in crystal growth from the vapor 109 (1991) 43
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Yamaga, S., A. Yoshikawa and H. Kasai, Growth and properties of iodine-doped ZnS films grown by low-pressure MOCVD using ethyliodide as a dopant source 106 (1990) 683
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Yamamoto, M., M. Oishi, H. Sudo, J. Nakano and N. Tsuzuki, Strained-layer InGaAs/InGaAsP MQW structures and their application to 1.67 μm lasers grown by metalorganic vapor phase epitaxy 107 (1991) 796
Yamamoto, N., N. Kondo and Y. Nanishi, Desorption process of Ga atoms from the mask surface in selective area growth of GaAs by electron-cyclotron-resonance plasma-excited molecular-beam epitaxy (ECR-MBE) 108 (1991) 433

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Yang Jianrong, Yu Zhenzhong, Liu Jiming and Tang Dingyuan, Heat treatment of HgCdTe with Cd–Hg source 101 (1990) 281
Yang, L., A.S. Sudbo, W.T. Tsang, P.A. Garbinski and R.M. Camarda, Monolithically integrated InGaAs/InP MSM–FET photo-receiver prepared by chemical beam epitaxy 105 (1990) 162
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Yodo, T., K. Ueda and K. Yamashita, p-Type doping by ion implantation into ZnSe epitaxial layers grown by metalorganic vapor phase epitaxy 101 (1990) 289
Yodo, T., K. Ueda, K. Morio, K. Yamashita and S. Tanaka, High quality over-epilayer growth of ZnSe on Li^+-implanted ZnSe epilayers by atmospheric pressure MOVPE 107 (1991) 659
Yokogawa, T., T. Saitoh and T. Narusawa, Effects of electric field on ZnSe/ZnS strained-layer superlattices 101 (1990) 550
Yokota, K., S. Tamura, T. Nakajima and S. Katayama, Low temperature deposition of single crystalline ZnSe films on GaAs substrates by slightly ionized molecular beams 109 (1991) 298
Yokota, T., see Yoshimura 102 (1990) 1035
Yokota, Y., H. Kawarada, J.S. Ma, K. Nishimura and A. Hiraki, Cathodoluminescence imaging of semiconducting diamond formed by plasma CVD 103 (1990) 65
Yokotani, A., A. Miyamoto, T. Sasaki and S. Nakai, Observation of optical inhomogeneities in flux grown KTP crystals 110 (1991) 963
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Yoshida, M., see Sugimoto 107 (1991) 692
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Yoshida, S., J. Suzuki, M. Nakayama and T. Kikuta, High quality SI-InP bulk crystal growth by horizontal gradient freeze method under controlled phosphorus vapor pressure 102 (1990) 696
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Yoshikawa, A., T. Okamoto, H. Yasuda, S. Yamaga and H. Kasai, "MBE-like" and "CVD-like" atomic layer epitaxy of ZnSe in MOMBE system 101 (1990) 86

Yoshikawa, A., S. Matsumoto, S. Yamaga and H. Kasai, Use of dimethyl hydrazine as a new acceptor-dopant source in metal-organic vapor phase epitaxy of ZnSe 101 (1990) 305
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Yoshikawa, A., T. Okamoto and T. Fujimoto, Effects of Ar ion laser irradiation on MOVPE of ZnSe using DMZn and DMSe as reactants 107 (1991) 653
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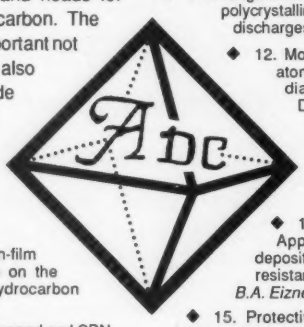

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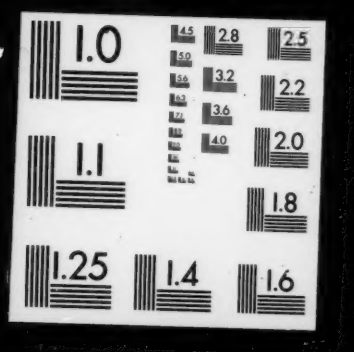
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